# 2SC5212

FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

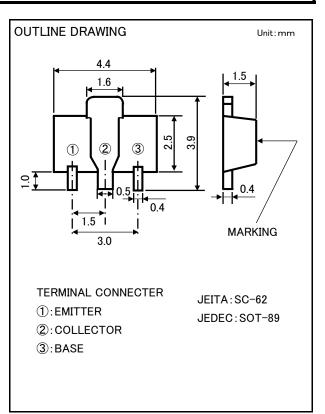
2SC5212 is a resin sealed silicon NPN epitaxial transistor. It designed with high collector current, small VCE(sat). Complementary with 2SA1946.

## FEATURE

- •Small package for easy mounting
- High collector current ICM=1000mA
- Low collector to emitter saturation voltage VCE(sat)=0.2V typ
- •Excellent linearity of DC forward current gain.
- High gain band with product fT=180MHz typ

## **APPLICATION**

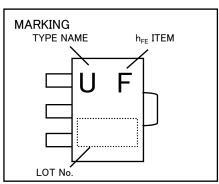
Small type motor drive, relay drive, power supply



## MAXIMUM RATINGS(Ta=25°C)

| Parameter                    | Symbol           | Ratings  | Unit |
|------------------------------|------------------|----------|------|
| Collector to Base voltage    | V <sub>CBO</sub> | 25       | V    |
| Emitter to Base voltage      | V <sub>EBO</sub> | 4        | V    |
| Collector to Emitter voltage | V <sub>CEO</sub> | 20       | V    |
| Collector current            | Ic               | 700      | mA   |
| Peak collector current       | I <sub>CM</sub>  | 1000     | mA   |
| Collector dissipation        | P <sub>c</sub>   | 500      | mW   |
| Junction temperature         | Tj               | +150     | °C   |
| Storage temperature          | $T_{stg}$        | -55~+150 | °C   |

## ELECTRICAL CHARACTERISTICS(Ta=25°C)



| Parameter                 | Symbol               | Test conditions                                   |     | Limits |     |      |
|---------------------------|----------------------|---|-----|--------|-----|------|
| Parameter                 | Symbol               | l est conditions                                  | Min | Тур    | Max | Unit |
| C to B breakdown voltage  | V(BR) <sub>CBO</sub> | $I_c=10 \mu$ A , $I_e=0$ mA                       | 25  | -      | -   | V    |
| E to B breakdown voltage  | V(BR) <sub>EBO</sub> | $I_{E}$ =10 $\mu$ A , $I_{C}$ =0mA                | 4   | -      | -   | V    |
| C to E breakdown voltage  | V(BR) <sub>CEO</sub> | $I_{C}$ =100 $\mu$ A , R <sub>BE</sub> = $\infty$ | 20  | -      | -   | V    |
| Collector cut off current | Ісво                 | V <sub>CB</sub> =25V, I <sub>E</sub> =0mA         | -   | -      | 1   | μA   |
| Emitter cut off current   | IEBO                 | $V_{EB}$ =2V, $I_{C}$ =0mA                        | -   | -      | 1   | μA   |
| DC forward current gain * | hFE                  | V <sub>CE</sub> =4V, I <sub>C</sub> =100mA        | 150 | -      | 800 | _    |
| C to E Saturation Voltage | VCE(sat)             | $I_c$ =500mA , $I_B$ =25mA                        | -   | 0.2    | 0.5 | V    |
| Gain bandwidth product    | fT                   | V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA        | -   | 180    | _   | MHz  |

 $\%\colon$  It shows hFE classification at right table.

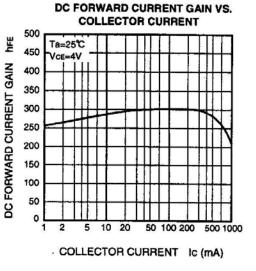
| Item | E       | F       | G       |  |
|------|---------|---------|---------|--|
| hFE  | 150~300 | 250~500 | 400~800 |  |

## 2SC5212

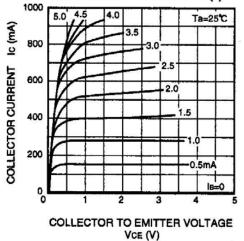
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#### COLLECTOR DISSIPATION VS AMBIENT TEMPERATURE 600 Pc(mW) 500 COLLECTOR DISSIPATION 400 300 200 100 0 0 25 50 75 100 125 150 AMBIENT TEMPERATURE Ta(°C)

TYPACAL CHARACTERISTICS



COMMON EMITTER OUTPUT (1)



 Ta=25°C

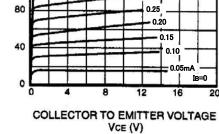
 160
 0.50

 120
 0.45

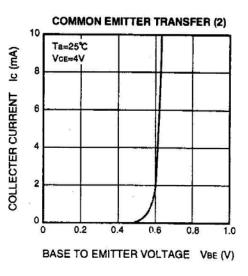
 120
 0.45

 0.35
 0.30

 80
 0.25



**COMMON EMITTER TRANSFER (1)** 1000 Ta=25°C Ic (mA) 900 VCE=4V 800 700 COLLECTOR CURRENT 600 500 400 300 200 100 0 0 0.2 0.4 0.6 0.8 1.0 BASE TO EMITTER VOLTAGE VBE (V)



COMMON EMITTER OUTPUT (2)

200

Ic (mA)

COLLECTOR CURRENT



6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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